



PATENT APPLICATION
Attorney's Do. No. 1138-71

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re divisional patent application of:

DAH WEN TSANG; JOHN W. MOSIER II, deceased;
DOUGLAS A. PIKE, JR. and
THEODORE O. MEYER

Examiner S. Loke

Serial No. 09/144,579

Group Art Unit 2811

Filed: August 31, 1998

For: SELF ALIGNED VERTICAL POWER MOSFET WITH
ENHANCED BASE REGION

Assistant Commissioner for Patents
Washington, D.C. 20231

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SUPPLEMENTAL AMENDMENT

Supplementing Applicant's response filed May 18, 2001, please amend the
application as follows:

In the claims:

Please amend claim 98 to read as follows:

Subt F⁴
fig. 13
E1

98. (Amended) A power MOSFET comprising:
a semiconductor substrate, the substrate comprising drain semiconductor material of a
first dopant type ;
source semiconductor material of a dopant type the same as said first dopant type;
channel semiconductor material of a second dopant type disposed between the source
semiconductor material and the drain semiconductor material, the channel semiconductor